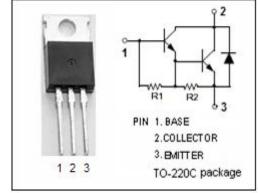


# isc Silicon NPN Darlington Power Transistor

2SD560

#### **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
- : V<sub>CEO(SUS)</sub>= 100V(Min)
- · High DC Current Gain
  - : h<sub>FE</sub>= 2000(Min) @I<sub>C</sub>= 3.0A
- Low Saturation Voltage
- Complement to Type 2SB601
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

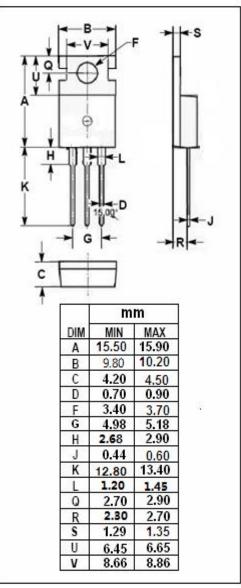


### **APPLICATIONS**

 Designed for low frequency power amplifiers and low speed switching applications

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	150	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
Ic	Collector Current-Continuous	5	А	
Іср	Collector Current-Peak	8	А	
I <sub>B</sub>	Base Current-Continuous	urrent-Continuous 0.5		
Pc	Collector Power Dissipation @ T <sub>a</sub> =25℃	1.5	W	
	Collector Power Dissipation @ T <sub>c</sub> =25℃	30		
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	





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#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 10mA;, I <sub>B</sub> =0	100			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 3mA		1.2	1.5	V		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 3mA		1.6	2.0	V		
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> =0			1	μА		
І <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> =0			3	mA		
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 3A ; V <sub>CE</sub> = 2V	2000	4000	15000			
h <sub>FE-2</sub>	DC Current Gain	Ic= 5A; Vc== 2V	500					
Switching times								
t <sub>on</sub>	Turn-on Time			0.5		μS		
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 3A , I <sub>B1</sub> = I <sub>B2</sub> = 3mA R <sub>L</sub> = 16.7 Ω ; V <sub>CC</sub> ≈50V		1.0		μS		
t <sub>f</sub>	Fall Time			1.0		μS		

### **NOTICE:**

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